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Supporting Information

Improved thermoelectric transport properties of Ge_4Se_3Te through dimensionality reduction

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Figure S1

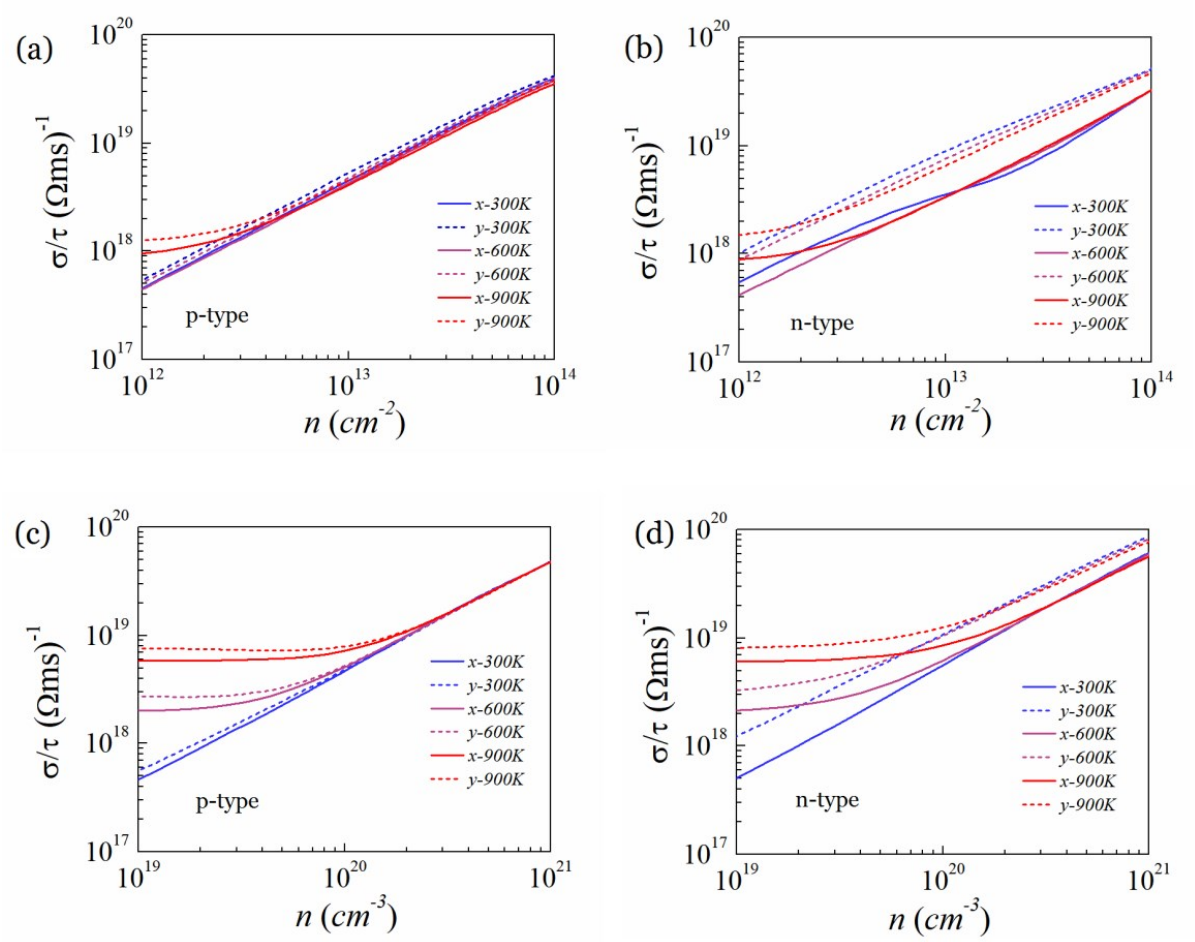

Fig.S1. Calculated the σ/τ of the monolayer and bulk Ge_4Se_3Te as a function of the carrier concentration along the *x* and *y* directions for (a, c) *p*-type and (b, d) *n*-type doping at different temperature

Figure S2

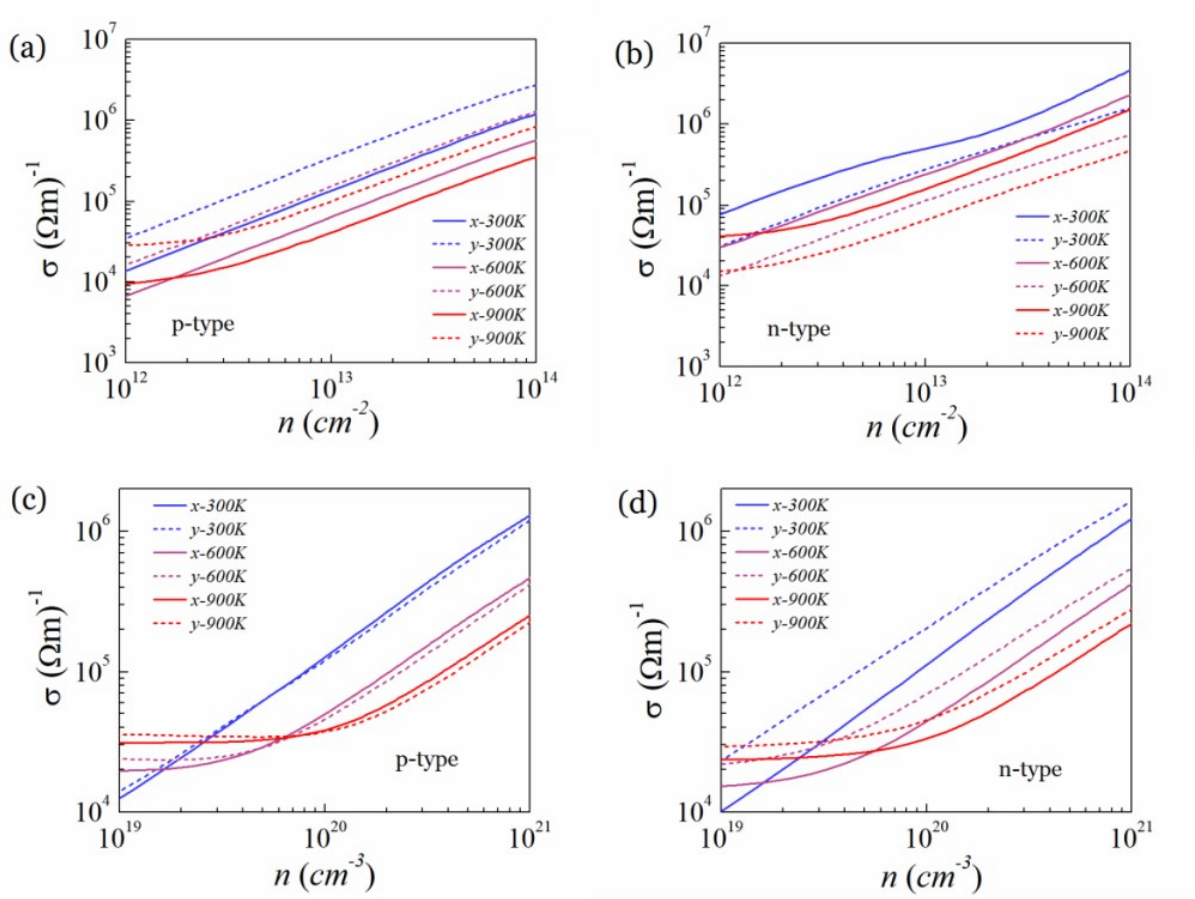

Fig.S2.The calculated carrier concentration-dependent electrical conductivity (σ) of *p*-type (a, c) and n-type (b, d) Ge_4Se_3Te monolayer and bulk at different temperature along *x* and *y* direction, respectively

Figure S3

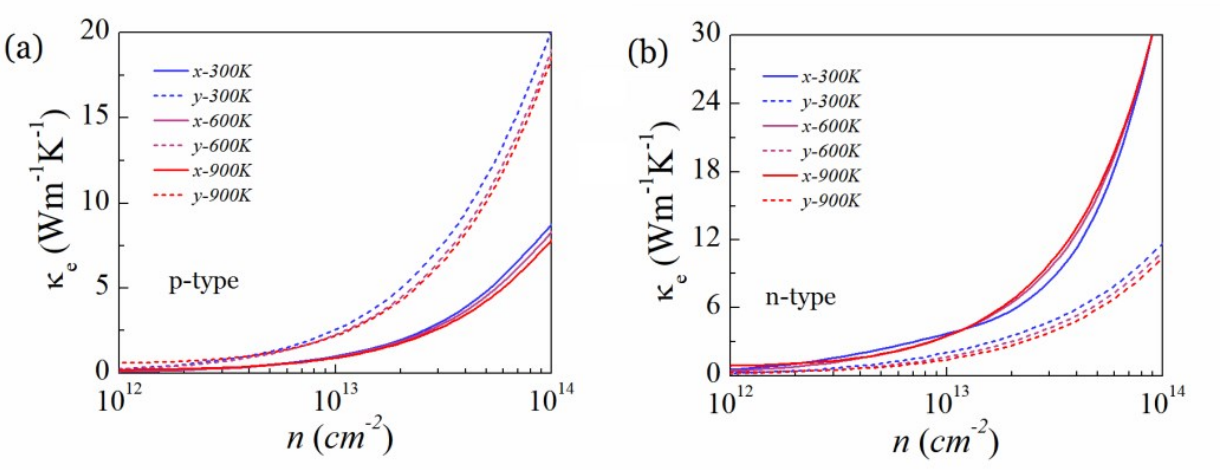

Fig.S3. Electronic thermal conductivity of Ge_4Se_3Te for the (a) *p*-type and (b) *n*-type doping